Halogen-Free

- Hi
- Very low switching losses
- Ig
- M

(Tc = 25°C unless otherwise specified)

$V_{DS,max}$	Drain source voltage	1200	V	V_{GS} = 0V, I_D

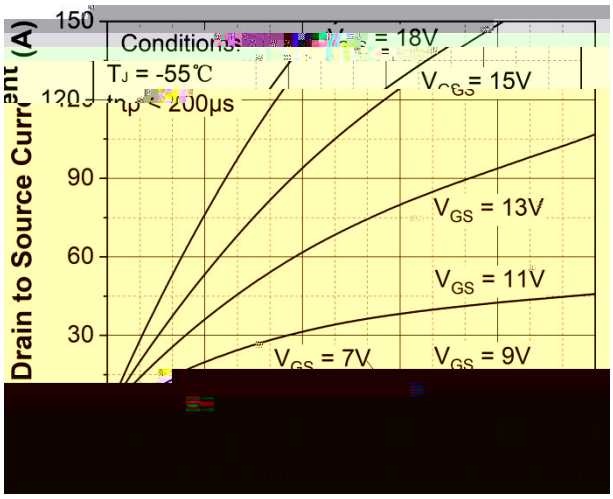


Figure 1. Output characteristics T_J = -55 ºC

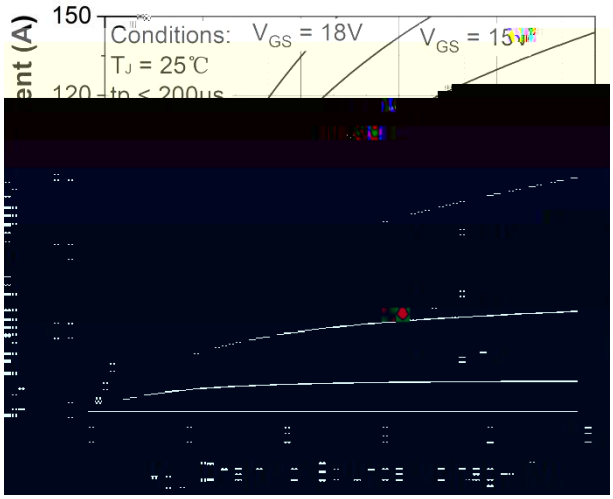


Figure 2. Output characteristics T_J = 25 ºC

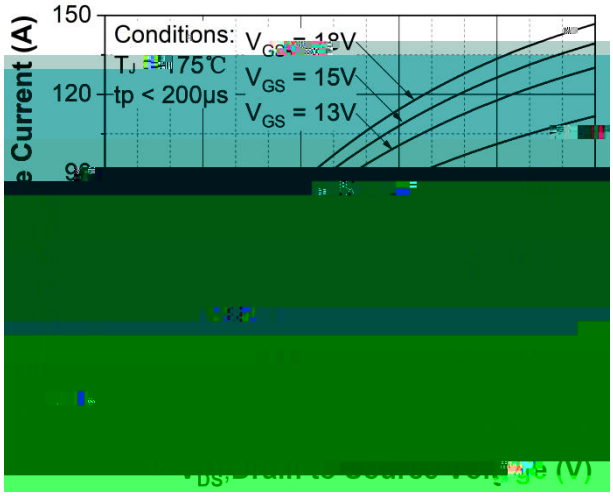


Figure 3. Output characteristics T_J = 175 ºC

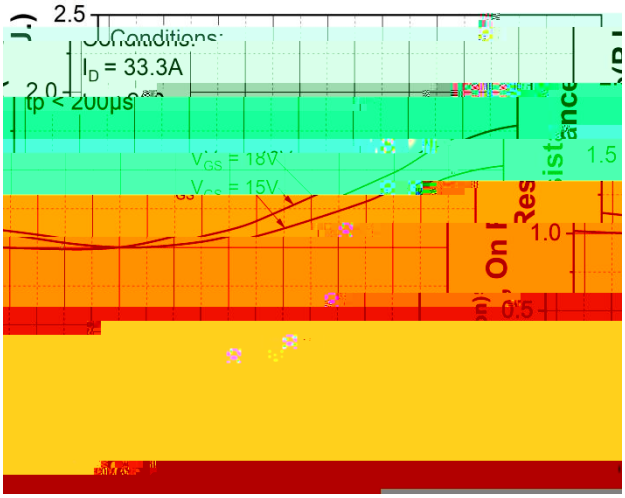


Figure 4. Normalized on-resistance vs. temperature

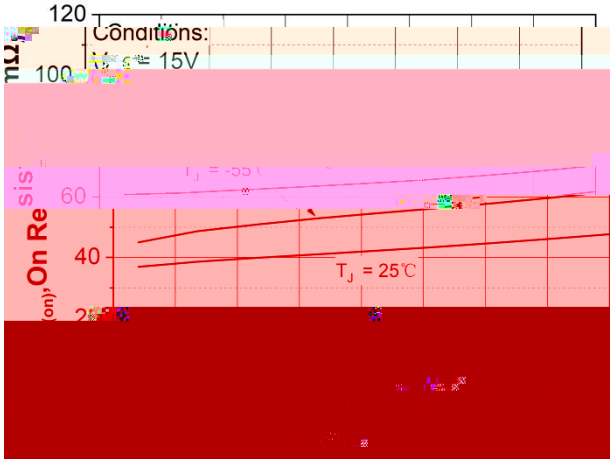


Figure 5. On-resistance vs. drain current for various temperatures

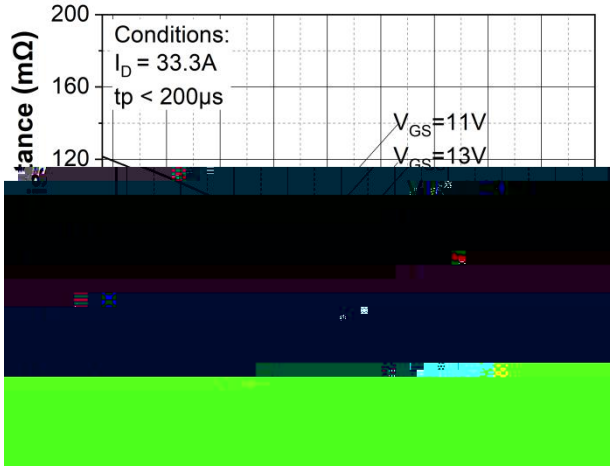


Figure 6. On-resistance vs. temperature for various gate voltage

Figure 7. Transfer

Figure 13 3rd

Figure 19. Continuous drain current derating vs. case temperature

Figure 20. Maximum power dissipation derating vs. case temperature

Figure 23. Clamped Inductive switching energy vs.

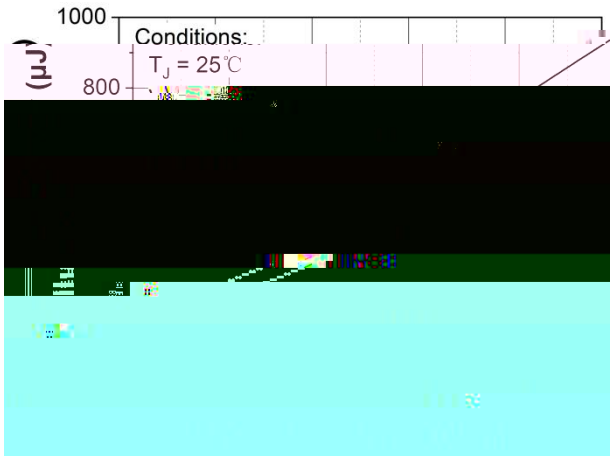


Figure 25. Clamped inductive switching energy vs. R_G(ext)

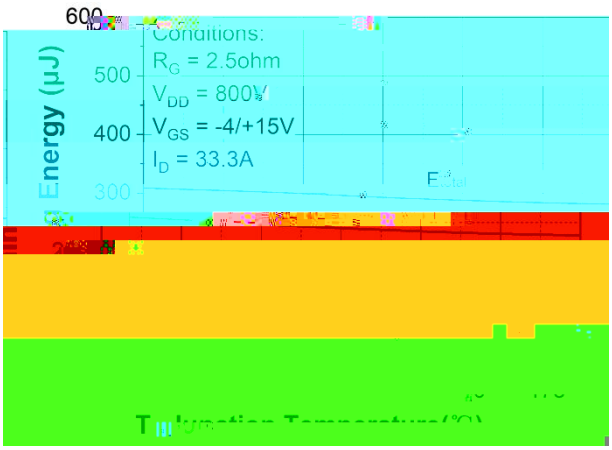


Figure 26. Clamped inductive switching energy vs. temperature

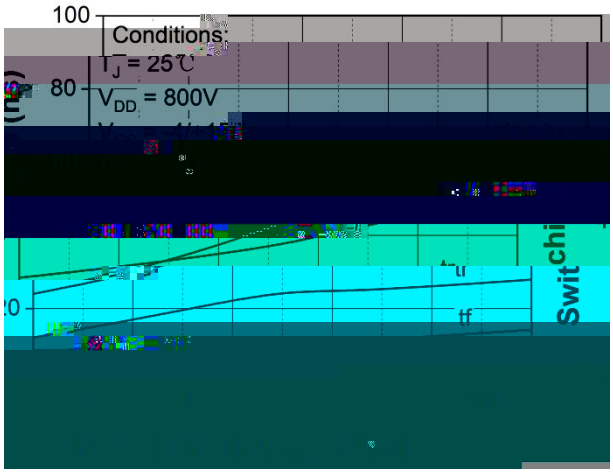
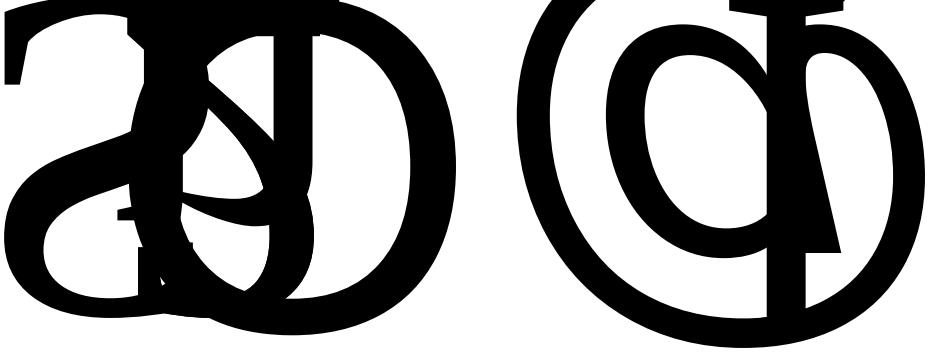


Figure 27. Switching times vs. R_G(ext)



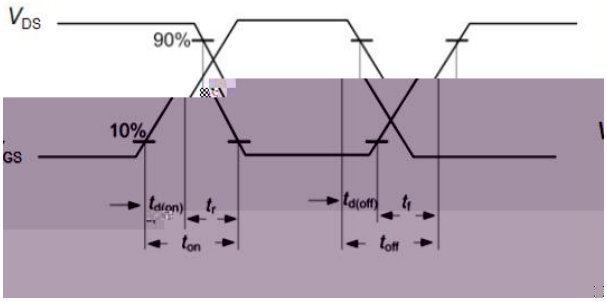


Figure A. Definition of switching times

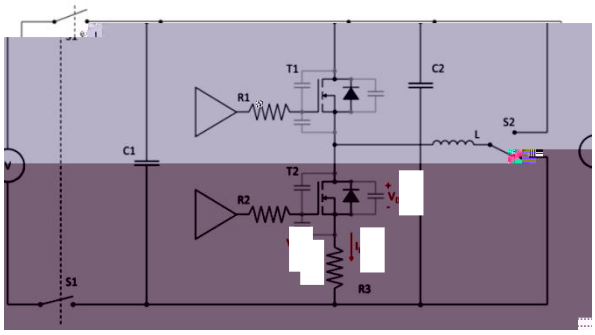


Figure B. Dynamic test circuit

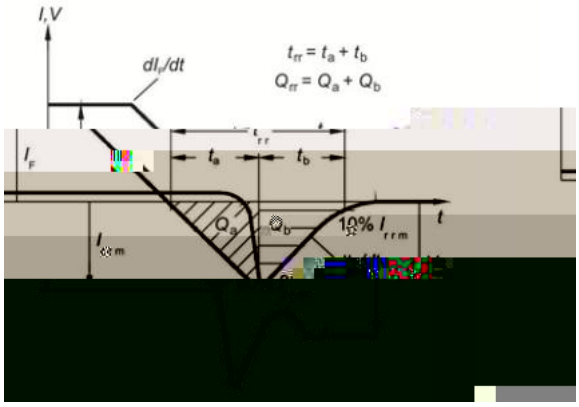


Figure C. Definition of body diode switching characteristics

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